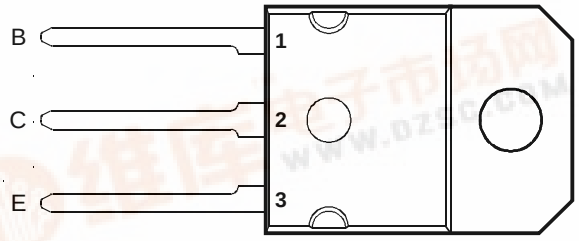
BDW83, BDW83A, BDW83B, BDW83C, BDW83D
NPN SILICON POWER DARLINGTONS

AUGUST 1978 - REVISED MARCH 1997

- **Designed for Complementary Use with BDW84, BDW84A, BDW84B, BDW84C and BDW84D**
- **150 W at 25°C Case Temperature**
- **15 A Continuous Collector Current**
- **Minimum h_{FE} of 750 at 3 V, 6 A**

SOT-93 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage (I_E = 0)	BDW83	V_{CBO}	45	V
	BDW83A		60	
	BDW83B		80	
	BDW83C		100	
	BDW83D		120	
Collector-emitter voltage (I_B = 0) (see Note 1)	BDW83	V_{CEO}	45	V
	BDW83A		60	
	BDW83B		80	
	BDW83C		100	
	BDW83D		120	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	15	A
Continuous base current		I_B	0.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	150	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$½LI_C^2$	100	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Operating temperature range		T_{stg}	-65 to +150	°C
Operating free-air temperature range		T_A	-65 to +150	°C

NOTES: 1. These values apply when the base-emitter diode is open circuited.
2. Derate linearly to 150°C case temperature at the rate of 1.2 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 5 mA, R_{BE} = 100 Ω, $V_{BE(off)}$ = 0, R_S = 0.1 Ω, V_{CC} = 20 V.

BDW83, BDW83A, BDW83B, BDW83C, BDW83D
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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS				MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C = 30 mA	I_B = 0	(see Note 5)	BDW83	45			V
					BDW83A	60			
					BDW83B	80			
					BDW83C	100			
					BDW83D	120			
I_{CEO}	Collector-emitter cut-off current	V_{CE} = 30 V	I_B = 0		BDW83			1	mA
		V_{CE} = 30 V	I_B = 0		BDW83A			1	
		V_{CE} = 40 V	I_B = 0		BDW83B			1	
		V_{CE} = 50 V	I_B = 0		BDW83C			1	
		V_{CE} = 60 V	I_B = 0		BDW83D			1	
I_{CBO}	Collector cut-off current	V_{CB} = 45 V	I_E = 0		BDW83			0.5	mA
		V_{CB} = 60 V	I_E = 0		BDW83A			0.5	
		V_{CB} = 80 V	I_E = 0		BDW83B			0.5	
		V_{CB} = 100 V	I_E = 0		BDW83C			0.5	
		V_{CB} = 120 V	I_E = 0		BDW83D			0.5	
		V_{CB} = 45 V	I_E = 0	T_C = 150°C	BDW83			5	
		V_{CB} = 60 V	I_E = 0	T_C = 150°C	BDW83A			5	
		V_{CB} = 80 V	I_E = 0	T_C = 150°C	BDW83B			5	
		V_{CB} = 100 V	I_E = 0	T_C = 150°C	BDW83C			5	
		V_{CB} = 120 V	I_E = 0	T_C = 150°C	BDW83D			5	
I_{EBO}	Emitter cut-off current	V_{EB} = 5 V	I_C = 0					2	mA
h_{FE}	Forward current transfer ratio	V_{CE} = 3 V	I_C = 6 A	(see Notes 5 and 6)		750		20000	
		V_{CE} = 3 V	I_C = 15 A			100			
$V_{BE(on)}$	Base-emitter voltage	V_{CE} = 3 V	I_C = 6 A	(see Notes 5 and 6)				2.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_B = 12 mA	I_C = 6 A	(see Notes 5 and 6)				2.5	V
		I_B = 150 mA	I_C = 15 A					4	
V_{EC}	Parallel diode forward voltage	I_E = 15 A	I_B = 0					3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, t_p = 300 µs, duty cycle ≤ 2%.
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			0.83	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on}	Turn-on time	I_C = 10 A	$I_{B(on)}$ = 40 mA	$I_{B(off)}$ = -40 mA		0.9		µs
t_{off}	Turn-off time	$V_{BE(off)}$ = -4.2 V	R_L = 3 Ω	t_p = 20 µs, dc ≤ 2%		7		µs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT

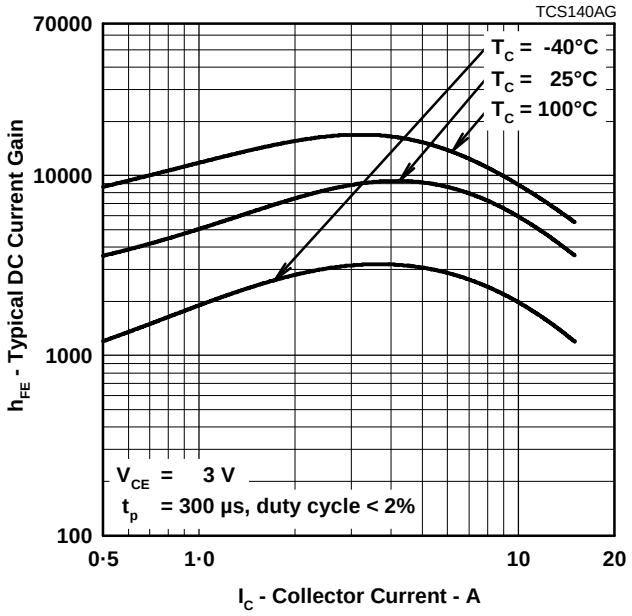

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

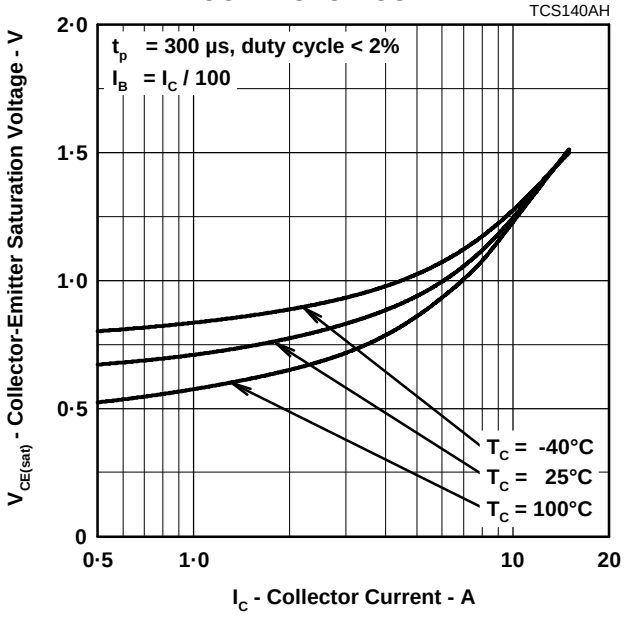

Figure 2.

BASE-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

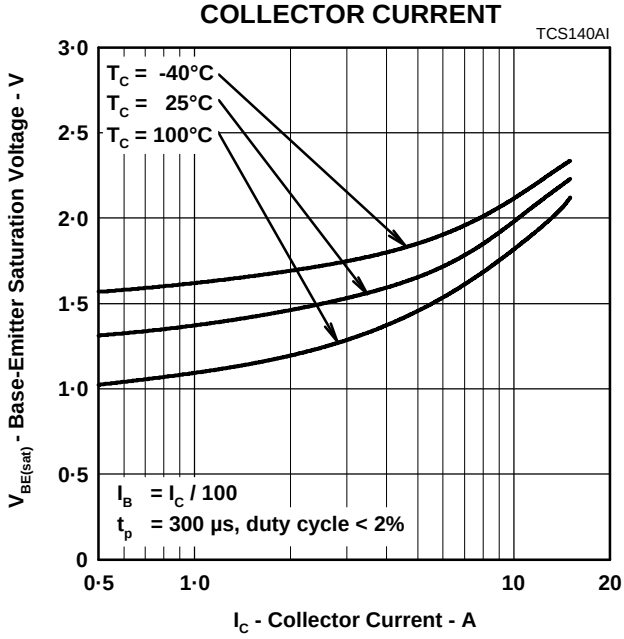

Figure 3.

MAXIMUM SAFE OPERATING REGIONS

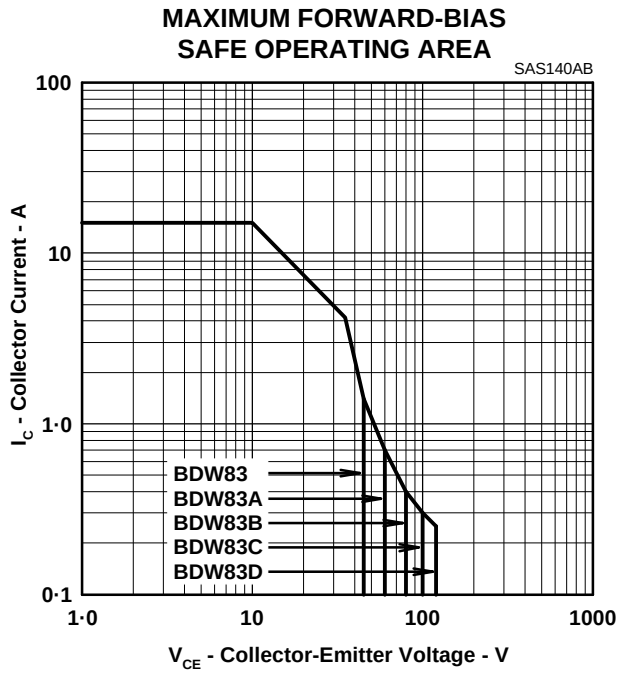

Figure 4.

THERMAL INFORMATION

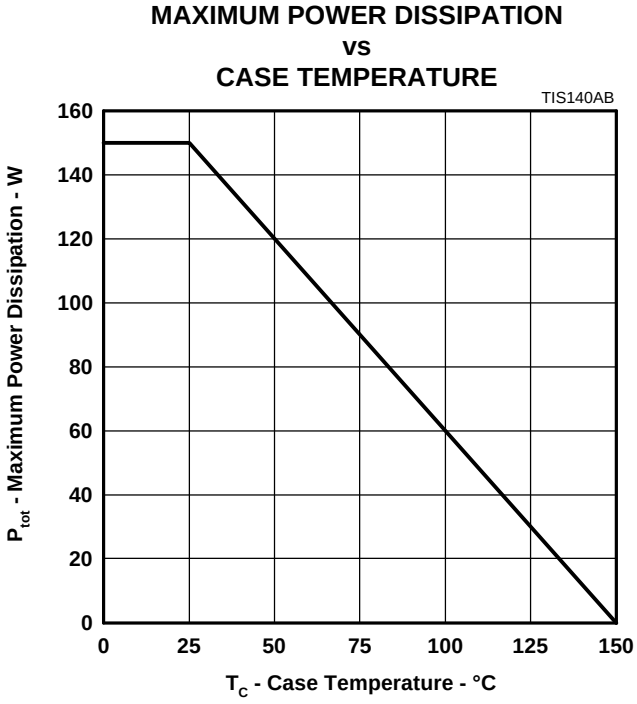

Figure 5.

BDW83, BDW83A, BDW83B, BDW83C, BDW83D
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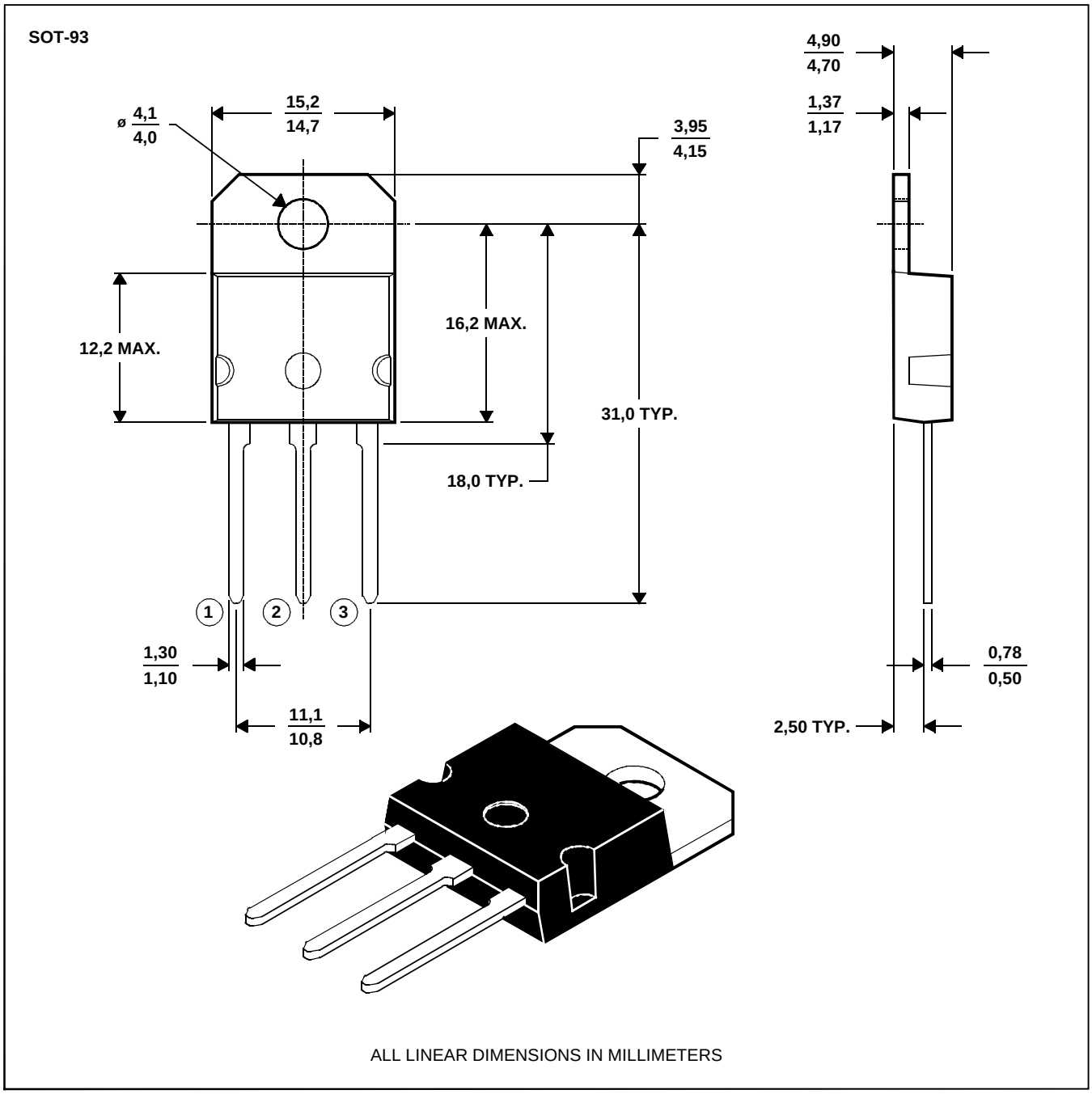
MECHANICAL DATA

SOT-93
3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAW

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